

U.S.S.N. 10,769,245

Specification Amendments

Please replace the Title of the Invention with the following:

~~##~~ POST-CMP CLEANING COMPOSITION AND METHOD

Please replace paragraph [0035] with the following rewritten paragraph:

[0035] Preferably, the surfactant composition solution is applied to a polished layer after the last polishing step in the polishing sequence. Most preferably, the surfactant composition solution is applied to a polished layer after each polishing step in the polishing sequence. The surfactant composition solution imparts a generally hydrophilic character to the layer, rendering the layer amenable to cleaning by deionized water. This significantly enhances the removal of particles from the layer and substantially reduces the number of CMP-induced defects. Furthermore, the surfactant composition solution stabilizes the polishing rate by cleaning the surface of the polishing pad on the CMP apparatus.

Please replace paragraph [0038] with the following rewritten

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paragraph:

[0038] The surfactant composition solution of the present invention may be an aqueous alcohol solution. Preferably, the alcohol is a C_4 - C_{12} alcohol. Most preferably, the alcohol is a C_{10} - C_{12} alcohol, having the formula $C_nH_{2n+1}OH$, where $n=10$, 11 or 12. In a preferred embodiment, the alcohol is octanol ($C_8H_{17}OH$) (C₂₀H₄₃OH).